

Figure of Merit of one-dimensional resonant transmission systems in the quantum regime

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Abstract

The figure of merit, ZT , for a one-dimensional conductor displaying a Lorentzian resonant transmission probability is calculated. The optimum working conditions for largest ZT values are determined. It is found that, the resonance energy has to be adjusted to be several resonance widths away from the Fermi level. Similarly it is better for the temperature to be equal to several resonance widths. The approximate relationships, which can be a fairly good guide for designing devices, between different parameters under optimum working conditions are given.

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I. INTRODUCTION

Recent advances in fabrication and material growth technologies have made possible the production of devices whose dimensions are order of a few nanometers. The thermoelectric power, thermal and electrical conductivities of these mesoscopic scale materials are of interest for thermoelectric device applications¹, such as heat pumps² and power generators. The performance of a thermoelectric device is usually quantified by a dimensionless number called as figure of merit, ZT , which measures the efficiency of thermoelectric energy conversion. Higher values of ZT correspond to higher thermoelectric energy conversion efficiency so that, for example, if ZT tends to infinity, the efficiency approaches to that of an ideal Carnot engine. Recent work on superlattice semiconducting devices demonstrated $ZT \approx 2.5$ at room temperature³ and $ZT \approx 1.4$ at high temperatures⁴, breaking the long-standing limit of $ZT \approx 1$ for most of best known thermoelectric materials.

In 1D nanoscale systems, the increase of ZT might be further enhanced by the quantum confining of electrons and phonons in low dimensions⁵. In the recent experimental study, for instance, ZT could be increased by embedding nanoparticles in a crystalline semiconductors⁶. High values of ZT can also be obtained for one-dimensional structures displaying resonant transmission. In this case, the transmission probabilities are very sensitive to the electron energies leading to large values of the thermopower and hence of the figure of merit. In this contribution, relationships between different thermoelectric coefficients are calculated, and probably the first, ZT values of a resonant tunnelling device is computed and its dependence on device parameters is investigated. We are expecting that our calculations will be a good guide to researchers studying on thermoelectric devices.

II. TRANSPORT COEFFICIENTS

In here a one-dimensional mesoscopic device is considered. It is assumed that there is only one transverse mode that is occupied by the electrons. The thermoelectric currents in such a device under linear regime can be expressed in terms of the energy dependent transmission probability $\mathcal{T}(E)$ of the electrons⁷. The electric current, I , and the heat current, \dot{Q} , under

a potential difference ΔV and a temperature difference ΔT can be expressed as⁸

$$I = \frac{2e^2}{h}g_0\Delta V + \frac{2(-e)k_B}{h}g_1\Delta T \quad , \quad (1)$$

$$\dot{Q} = \frac{2(-e)k_BT}{h}g_1\Delta V + \frac{2k_B^2T}{h}g_2\Delta T \quad , \quad (2)$$

where g_n are

$$g_n = \int_{-\mu/k_BT}^{\infty} dx \, x^n (-f'(x)) \mathcal{T}(\mu + xk_BT) \quad , \quad (3)$$

μ is the chemical potential and $f(x) = 1/(1 + e^x)$ is the Fermi-Dirac distribution function.

Frequently measured transport coefficients, the electrical conductance G_{el} , the thermal conductance G_{th} , the Seebeck coefficient S , and the dimensionless thermoelectric figure of merit ZT can be expressed as

$$G_{\text{el}} = \frac{2e^2}{h}g_0 \quad , \quad (4)$$

$$G_{\text{th}} = \frac{2k_B^2}{h}T \left(g_2 - \frac{g_1^2}{g_0} \right) \quad , \quad (5)$$

$$S = \frac{k_B}{(-e)} \frac{g_1}{g_0} \quad , \quad (6)$$

$$ZT = \frac{S^2 G_{\text{el}} T}{G_{\text{th}}} = \frac{g_1^2}{g_0 g_2 - g_1^2} \quad . \quad (7)$$

It can be seen that, to obtain large values of ZT , the factor g_1 , which also appears in the Seebeck coefficient, has to be large. Equation (3) implies that at low temperatures, g_1 is basically proportional to the first derivative of $\mathcal{T}(E)$. For this reason, large values of g_1 can be achieved when $\mathcal{T}(E)$ is strongly energy dependent, and the fastest change in it occurs around the Fermi level. In this contribution we investigate a resonant tunnelling device where the transmission probability is assumed to have a Lorentzian form

$$\mathcal{T}(E) = \frac{\mathcal{T}_{\text{max}}}{1 + (E - E_o)^2/\Gamma^2} \quad , \quad (8)$$

where E_o is the resonance energy and Γ is the half width. The factor g_1 and the Seebeck coefficient S changes sign when the Fermi energy crosses the resonance energy E_o . However, when μ differs from E_o by an energy of the order of Γ , both of these quantities attain large values and this is the region where we should look for large values of ZT . It is assumed that the Fermi level is very large compared to the temperature so that the lower limit of the integral in Eq. (3) is extended to minus infinity.

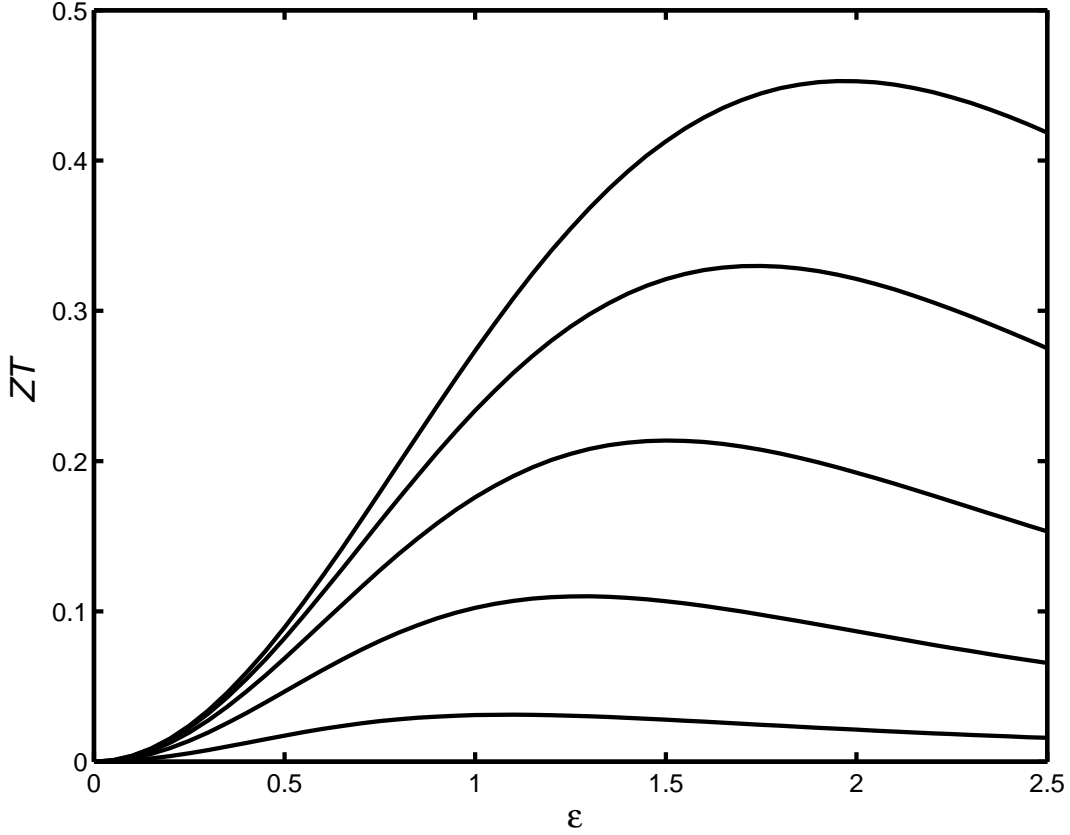


FIG. 1: Variation of ZT for different values of temperature ($\theta = 0.1, 0.2, 0.3, 0.4, 0.5$ from bottom to top) as a function of ϵ .

III. RESULTS AND DISCUSSION

It can be seen that the values of ZT depend on two dimensionless parameters. One of them, $\epsilon = (\mu - E_o)/\Gamma$, indicates the distance of the Fermi level from the resonance energy in units of the half width Γ , and the other, $\theta = k_B T/\Gamma$ gives the temperature compared to the resonance width.

The values of ZT as a function of dimensionless Fermi level, ϵ , for different temperatures is shown in Fig. 1. The Seebeck coefficient is zero at $\epsilon = 0$ and has different signs at different sides of this point. Since ZT is an even function of ϵ , only the positive values of ϵ is shown in the figure. It can be seen that when ϵ is varied, ZT values increase, reach a maximum and then start to decrease. The place and the value of the maxima depends on the temperature.

The maximum attainable value of figure of merit, ZT_{\max} and the best place of Fermi level, ϵ_{\max} for each temperature are plotted in Fig. (2). For low temperatures, $\lesssim 0.1$, the best place

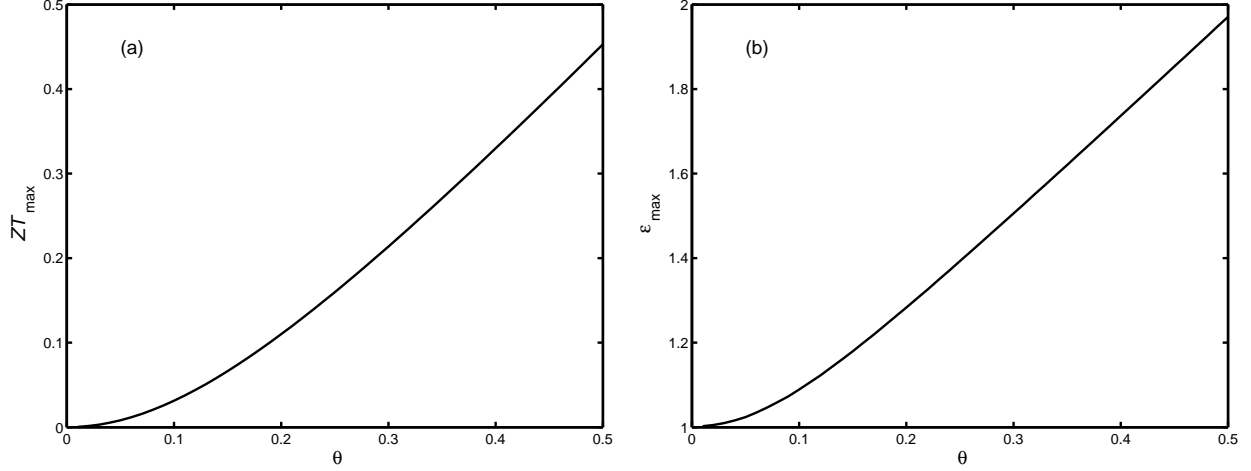


FIG. 2: (a) The maximum values of ZT as a function of μ is plotted for different values of θ . (b) The value of ϵ at maxima is plotted for different values of θ .

of the Fermi level is approximately one resonance width above or below of the resonance energy ($\epsilon \approx \pm 1$), but the maximum attainable figure of merit value is very low. For high temperatures however, both of these parameters have a linear dependence on temperature which are approximately given as

$$\epsilon_{\max} \approx 0.8 + 2.4\theta \quad , \quad (9)$$

$$ZT_{\max} \approx 1.4\theta - 0.3 \quad . \quad (10)$$

It can be seen that, in each case the optimum value of the figure of merit is obtained when $|\epsilon| > 1$, i.e., the Fermi level should be more than one half-width away from the resonance energy. If the Lorentzian form of the resonance in Eq. (8) remains valid for a large energy interval, sufficiently large ZT values can be obtained in this domain.

The values of ZT as a function of θ for different places of the Fermi level is shown in Fig. 3. The figure of merit reaches a maximum for a certain temperature in this case as well. The maximum attainable value of figure of merit, ZT_{\max} and the optimum temperature, θ_{\max} are shown in Fig. (4) as a function of ϵ . When the Fermi level is almost coincident with the resonance energy ($\epsilon \lesssim 1$), the temperature at which maximum attained is around $\theta \approx 0.6$. However, in this region, ZT values are low. In the opposite case, for $\epsilon \gtrsim 1$, the optimum temperature and the best value of ZT appear to be linear in ϵ with the following

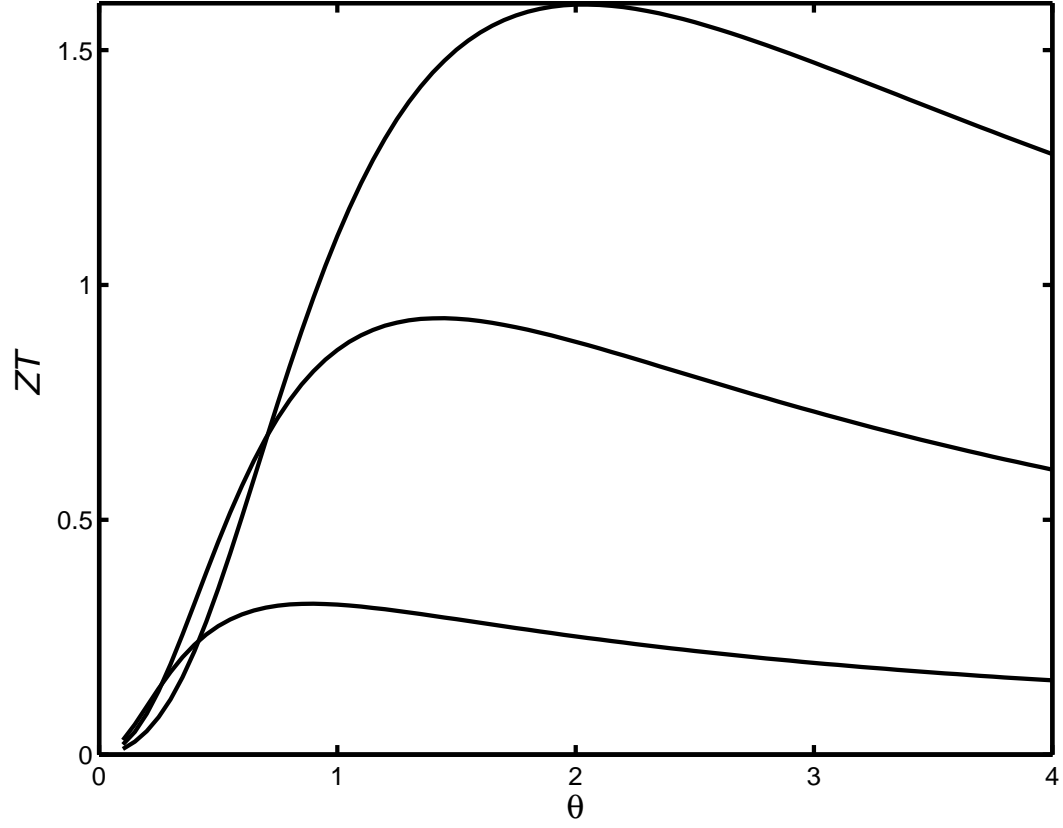


FIG. 3: Variation of ZT for different placements of the Fermi level ($\epsilon = 1, 2, 3$ from bottom to top) as a function of θ .

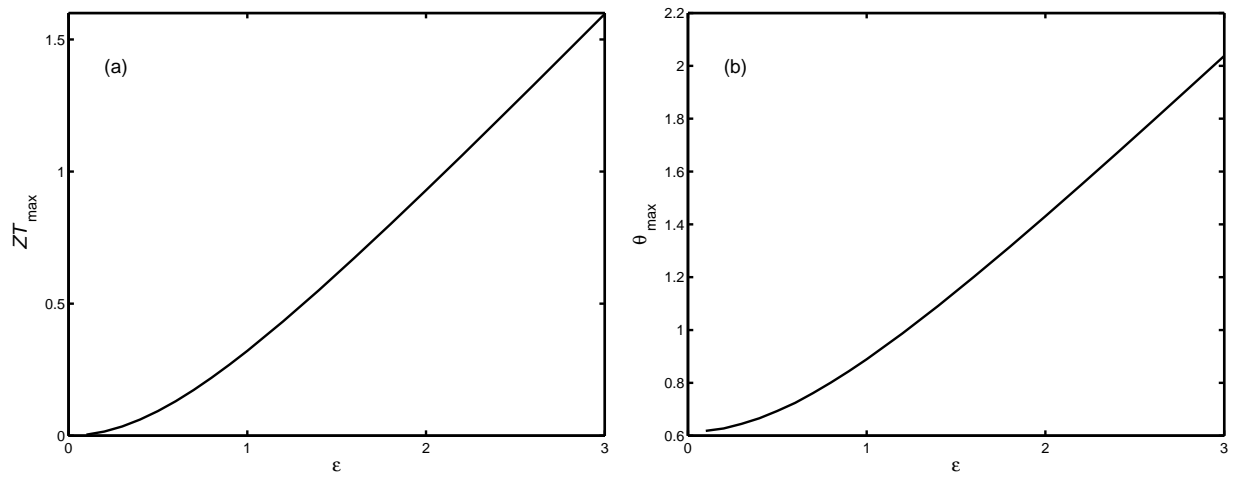


FIG. 4: (a) The maximum values of ZT as temperature is varied is plotted as a function of ϵ . (b) The value of θ at maxima is plotted as a function of ϵ .

numerical relationships

$$\theta_{\max} \approx 0.6\epsilon + 0.2 \quad , \quad (11)$$

$$ZT_{\max} \approx 0.7\epsilon - 0.4 \quad . \quad (12)$$

The approximate relation $\theta_{\max} \approx 0.9ZT_{\max} + 0.6$ seems to hold over the whole range investigated in this study.

It is seen that for one-dimensional systems displaying resonant transmission, it is possible to obtain large values of the figure of merit ZT by fine-tuning the device parameters, the resonance width and the place of the resonance energy relative to the Fermi level. The optimum working conditions for the largest values of ZT appears to be far away from the resonance: Fermi level is several Γ away from the resonance energy E_o and $k_B T$ is several times Γ . It can be argued that, under such extreme cases, the validity of Lorentzian form in Eq. (8) is questionable and some of the results obtained in here can be changed. However, the crucial feature leading to these results is the strong energy dependence of the transmission probability. Specifically, the transmission probability should continue decreasing at the Fermi level and not reach to a minimum. For this reason, similar results can be expected for realistic devices. Numerical computations for a double barrier system displaying resonances indicate that when the half width Γ is much smaller than the distance between the resonances, results obtained are roughly in agreement with the ones in here. For this reason Lorentzian form can be used as a fairly good guide for designing devices.

An important problem, connected with being far away from the resonance, is the smallness of the electrical and thermal conductances. For this reason, efficient devices can only work with very small power. Moreover, precautions should be taken to make the phonon contribution to the heat conductance to be very small as this will always decrease the ZT value.

IV. CONCLUSIONS

The figure of merit has been computed for a system whose transmission probability displays a Lorentzian peak. By adjusting the resonance width to be small and carefully placing the Fermi level for the working temperatures of interest, significantly high values of ZT can be obtained. Approximate numerical relationships, which can be a guide for

designing thermoelectric devices, for the optimum values of the parameters are also given.

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